MDF10N055TH

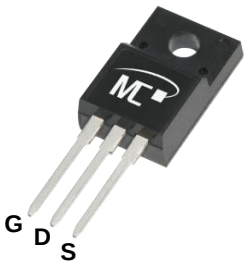
Single N-channel Trench MOSFET 100V 5.5mΩ 80A

General description

The MDF10N055TH uses advanced MagnaChip's MOSFET Technology, which provides high performance in on-state resistance, fast switching performance, and excellent quality.

These devices can also be utilized in industrial applications such as Synchronous Rectification and general Purpose applications.

TO-220F



Top View

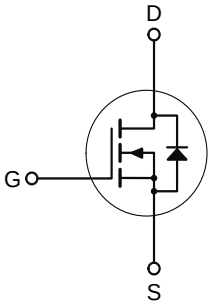
Bottom View

Features and benefits

- **MagnaChip's MOSFET Technology**
- **Very low on-resistance $R_{DS(on)}$**
- **100% Avalanche / Rg Tested**

Applications

- **Specifically for Syncronous Rectification**
- **Switching Applications**



Key performance parameters

V_{DS}	**100**	V
$R_{DS(on),\ max}$	**0.0055**	Ω
I_D	**80**	A
Q_G	**85**	nC
Junction temperature, max	**175**	°C

RoHS Compliant
HALOGEN-FREE

Ordering information

Type / Ordering Code	Package	Marking	Packing	RoHS Status
MDF10N055TH	TO-220F	10N055	Tube	Halogen Free

http://www.magnachip.com/powersolutions

MX LISTED NYSE

Maximum ratings, at T_A = 25°C, unless otherwise specified

Parameter		Symbol	Rating	Unit
Drain-source Voltage		V_{DS}	100	V
Gate-source Voltage		V_{GS}	± 20	V
Drain current	Tc=25°C Silicon Limited	I_D	80	A
	Tc=25°C Package Limited		80	A
	Tc=100°C Silicon Limited		56	A
1) Pulsed drain current	Tc=25°C	I_{DM}	320	A
Total power dissipation	Tc=25°C	P_{tot}	70	W
	Tc=100°C		35	W
2) Avalanche energy, single pulse		E_{AS}	288	mJ
Operating and storage temperature		T_j, T_{stg}	- 55 ~ 175	°C

Thermal characteristics

Parameter	Symbol	Rating	Unit
Thermal resistance, junction - case	$R_{\theta JC}$	2.15	K/W
3) Thermal resistance, junction - ambient	$R_{\theta JA}$	62.5	K/W

Notes

1. Pulse width limited by Tjmax
2. EAS is tested at starting Tj = 25℃, L = 1.0mH, I_{AS} = 24A, V_{DD} = 50V, V_{GS} = 10V
3. Surface mounted FR-4 board by JEDEC (jesd51-7)

Electrical Characteristics (T_J = 25°C)

Static characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions / Note
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	V_{GS}=0 V, I_D=250 μA
Gate threshold voltage	$V_{GS(th)}$	2.0	2.8	4.0	V	V_{DS}=V_{GS}, I_D=250 μA
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	V_{DS}=100 V, V_{GS}=0 V
Gate-source leakage current	I_{GSS}	-	-	± 100	nA	V_{GS}=±20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	-	4.5	5.5	mΩ	V_{GS}=10 V, I_D=40 A
Gate resistance	R_G	-	2.5	-	Ω	f=1MHz
Transconductance	g_{fs}	-	80	-	S	V_{DS}=10 V, I_D=40 A

Dynamic characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions / Note
Input capacitance	C_{iss}	-	5,840	-	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Output capacitance	C_{oss}	-	1,030	-	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Reverse transfer capacitance	C_{rss}	-	35	-	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Turn-on delay time	$t_{d(on)}$	-	24	-	ns	V_{DD}=50 V, V_{GS}=10 V, ID=40 A, $R_{G,ext}$=3Ω
Rise time	t_r	-	12	-	ns	V_{DD}=50 V, V_{GS}=10 V, ID=40 A, $R_{G,ext}$=3Ω
Turn-off delay time	$t_{d(off)}$	-	65	-	ns	V_{DD}=50 V, V_{GS}=10 V, ID=40 A, $R_{G,ext}$=3Ω
Fall time	t_f	-	15	-	ns	V_{DD}=50 V, V_{GS}=10 V, ID=40 A, $R_{G,ext}$=3Ω

Gate charge characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions / Note
Gate to source charge	Q_{gs}	-	23	-	nC	V_{DD}=50 V, I_D=40 A, V_{GS}=0 to 10 V
Gate charge at threshold	$Q_{gs(th)}$	-	16	-	nC	V_{DD}=50 V, I_D=40 A, V_{GS}=0 to 10 V
Gate to drain charge	Q_{gd}	-	17	-	nC	V_{DD}=50 V, I_D=40 A, V_{GS}=0 to 10 V
Switching charge	Q_{sw}	-	24	-	nC	V_{DD}=50 V, I_D=40 A, V_{GS}=0 to 10 V
Gate charge total	Q_g	-	85	-	nC	V_{DD}=50 V, I_D=40 A, V_{GS}=0 to 10 V
Gate plateau voltage	$V_{plateau}$	-	4.3	-	V	V_{DD}=50 V, I_D=40 A, V_{GS}=0 to 10 V

Source-drain diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions / Note
Diode continous forward current	I_S	-	-	80	A	-
Diode pulse current	$I_{S,pulse}$	-	-	320	A	pulsed; tp ≤ 10 μs
Diode forward voltage	V_{SD}	-	0.9	1.2	V	V_{GS}=0 V, I_F=40 A
Reverse recovery time	t_{rr}	-	80	-	ns	I_F=40 A, d_{iF}/dt=100 A/μs
Reverse recovery charge	Q_{rr}	-	240	-	nC	I_F=40 A, d_{iF}/dt=100 A/μs

Electrical characteristics diagrams

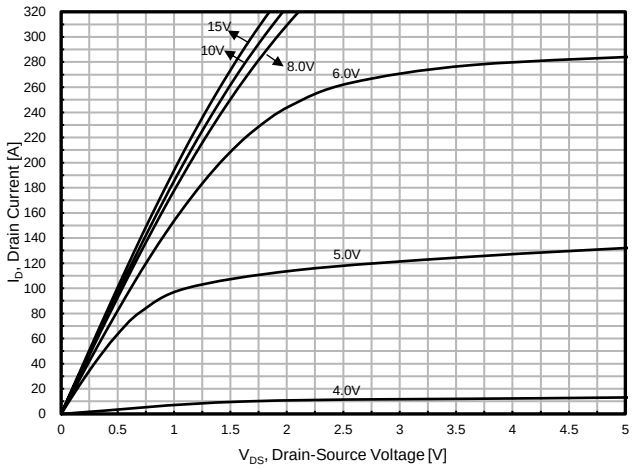


Fig. 1. Output Characteristics

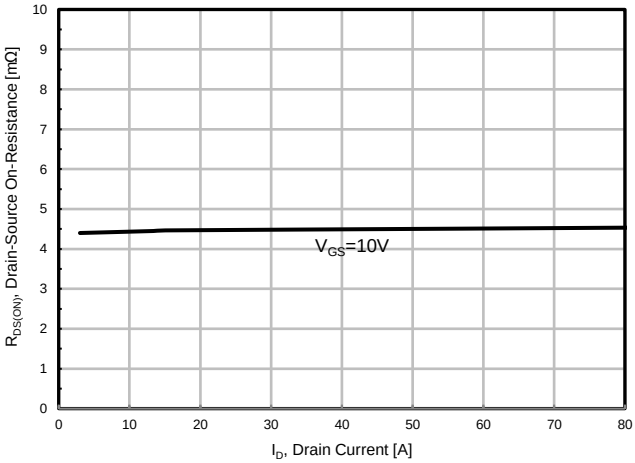


Fig. 2. Static On-Resistance Variation

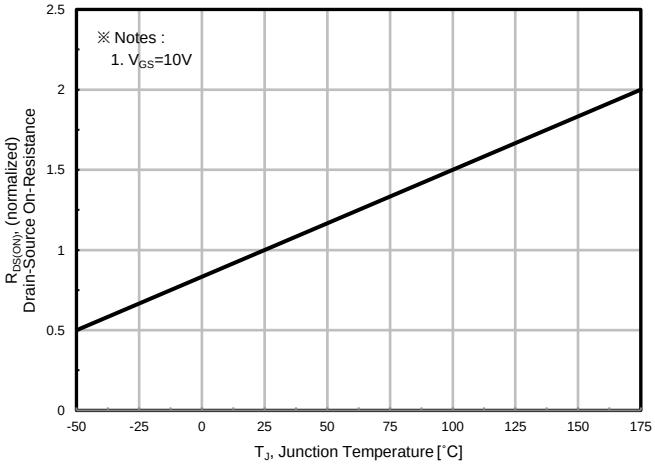


Fig. 3. On-Resistance vs. Junction Temperature

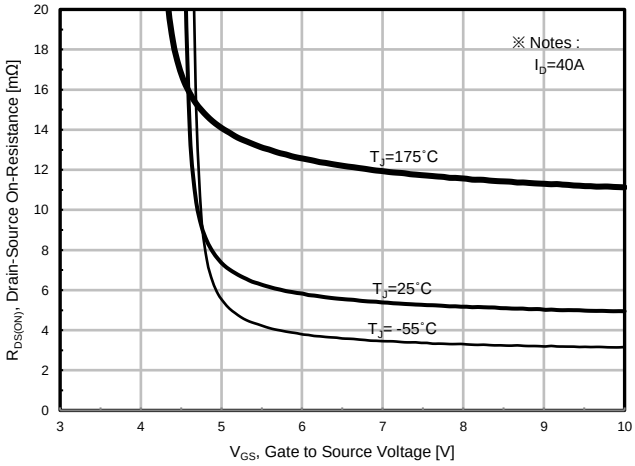


Fig. 4. On-Resistance vs. Gate to Source Voltage

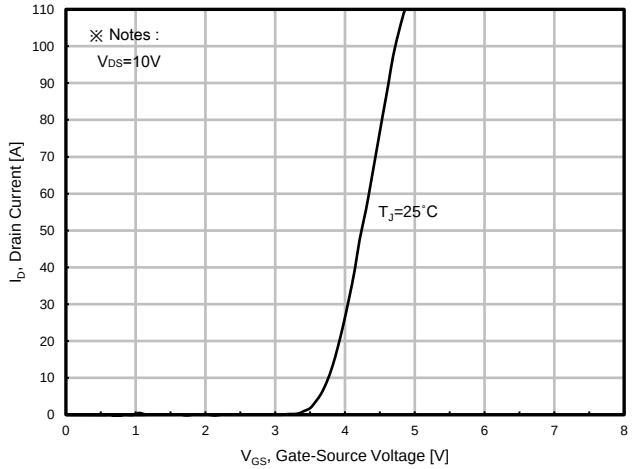


Fig. 5. Transfer Characteristics

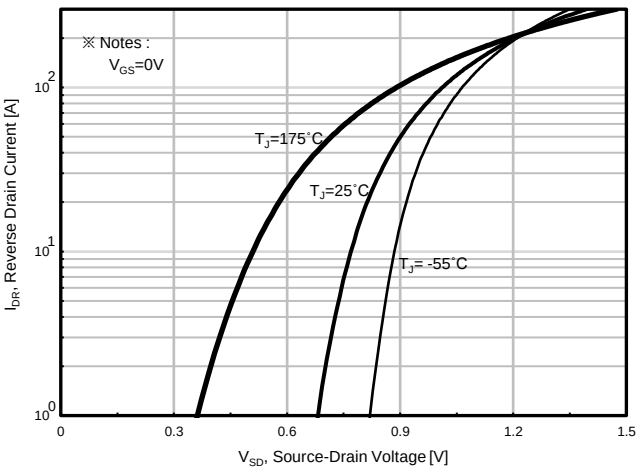


Fig. 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Electrical characteristics diagrams

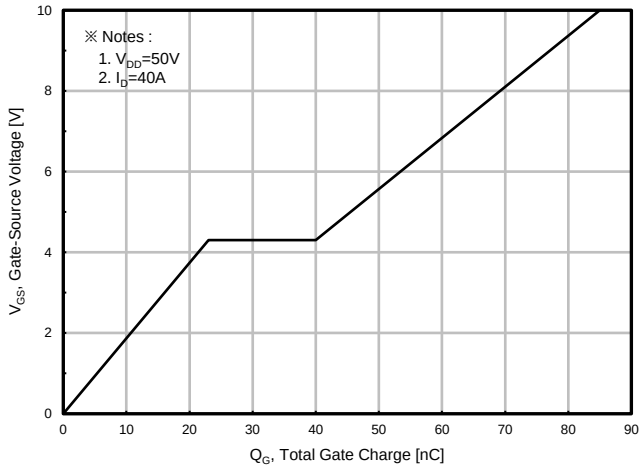


Fig. 7. Gate Charge

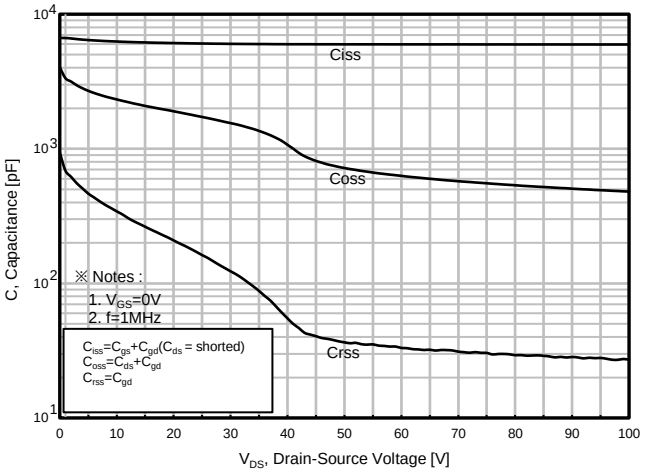


Fig. 8. Capacitances

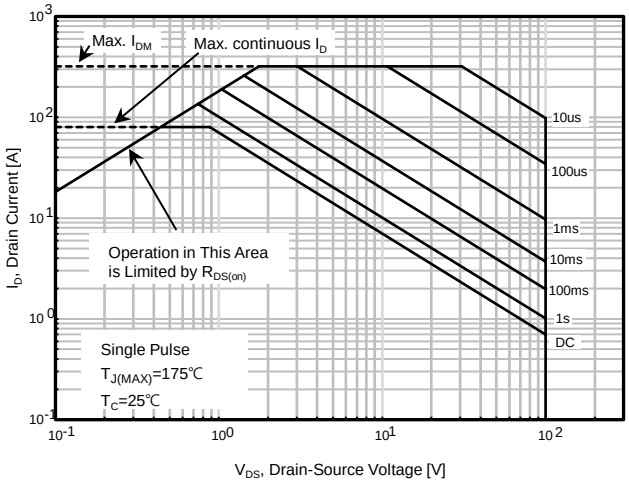


Fig. 9. Safe Operating Area

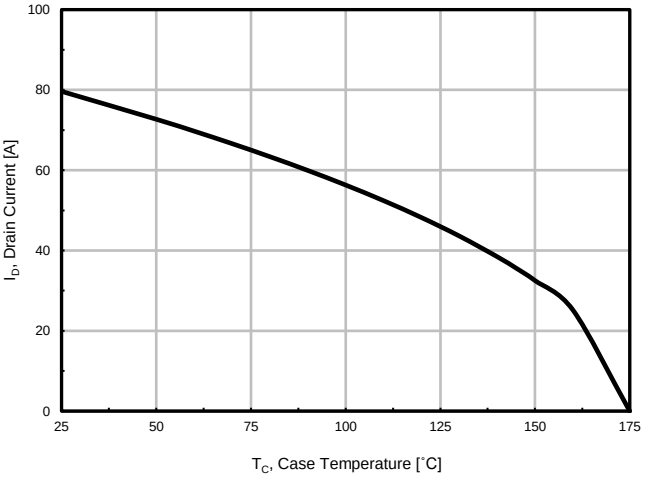


Fig. 10. Maximum Drain Current vs. Case Temperature

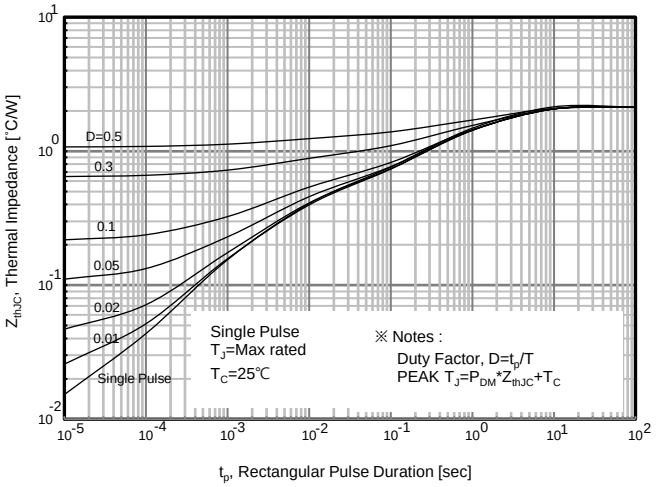
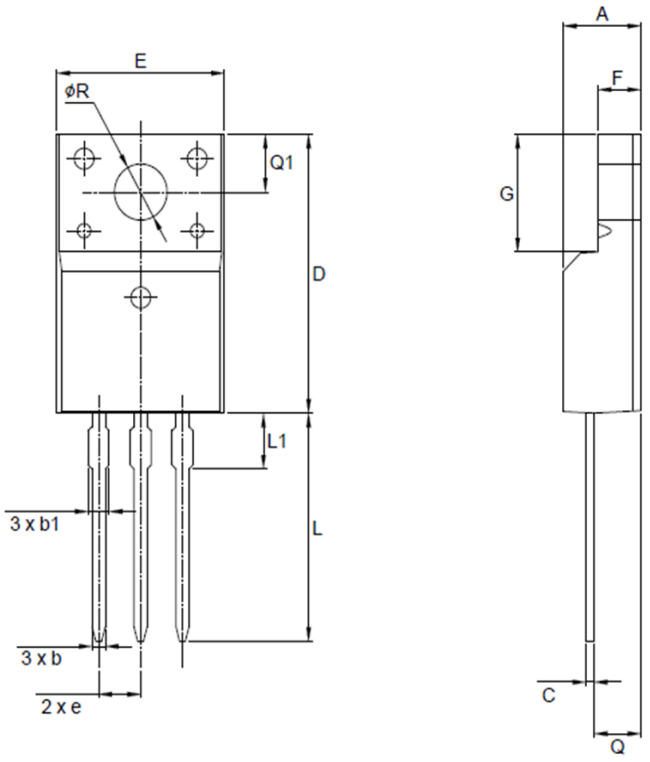


Fig. 11. Transient Thermal Impedance

Package information

TO-220F



Symbol	Dimension (mm)		
	Min	Nom	Max
A	4.50	–	4.93
b	0.63	–	0.91
b1	1.15	–	1.47
C	0.33	–	0.63
D	15.47	–	16.13
E	9.60	–	10.71
e	2.54 BSC		
F	2.34	–	2.84
G	6.48	–	6.90
L	12.24	–	13.72
L1	2.79	–	3.67
Q	2.52	–	2.96
Q1	3.10	–	3.50
øR	3.00	–	3.55

Notes

PKG dimension does not include mold burr and flash

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